

12NS/12NSR

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12AMP SILICON POWER DIODE



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DO-4

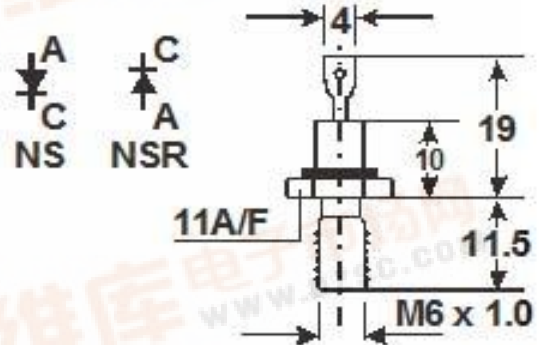
FEATURES

- All Diffused Series
- Available in Normal & Reverse Polarity
- Industrial Grade
- Available In Avalanche Characteristic

ELECTRICAL SPECIFICATIONS

12NS/NSR		
I_F (A)	Maximum Average Forward Current $T_c = 150^\circ\text{C}$	12A
V_{FM}	Maximum peak forward voltage drop @ Rated I_F	1.2V
I_{FSM}	Maximum peak one cycle (non-rep) surge current 10msec	250A
I_{RSM}	Maximum peak one cycle (non-rep) surge current 10msec	60A
I^2t	Maximum I^2t rating (non-rep.) for 5 to 10 m sec.	250A ² Sec

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THERMAL MECHANICAL SPECIFICATIONS

θ_{JC}	Maximum thermal resistance Junction to case	2°C/W
T_J	Operating Junction Temp.	-65°C to 150°C
T_{stg}	Storage temperature	-65°C to 150°C
	Mounting torque (non-lubricated threads)	0.14 M-Kg min, 0.17 M-kg max
W	Approx, weight	7 gms.

ELECTRICAL RATINGS

TYPE	12NS/12NSR	10	20	40	60	80	100	120	140	160
V_{RRM}	Max. repetitive peak voltage (v)	100	200	400	600	800	1000	1200	1400	1600
V_R (RMS)	Max. R.M.S. reverse voltage (V)	70	140	280	420	560	700	840	980	1120
V_R	Max. D.C. Blocking Voltage (V)	100	200	400	600	800	1000	1200	1400	1600
	Recommended R.M.S. working Voltage(v)	40	80	160	240	320	400	480	560	640
I_R (AV)	Max. Average reverse leakage current @ V_{RMM} T_c 25°C μA	100	100	100	100	100	100	100	100	100